

CLAIMS

1. A semiconductor polishing composition comprising:
fumed silica, the semiconductor polishing composition
being an aqueous dispersion solution of fumed silica,
wherein an increase rate of average particle diameter
of fumed silica after a shake test for 10 days is 10% or less
2. The semiconductor polishing composition of claim 1,
wherein a content of the fumed silica is in a range of 10 to
30% by weight based on a total amount of the composition.
3. The semiconductor polishing composition of claim 1 or
2, wherein the average particle diameter of the fumed silica
is in a range of 70 to 110 nm.
4. The semiconductor polishing composition of any one of
claims 1 to 3, wherein the semiconductor polishing composition
is prepared by adding an acidic fumed silica dispersion solution
to an alkali aqueous solution.
5. The semiconductor polishing composition of claim 4,
wherein a pH of the alkali aqueous solution is in a range of
12 to 14.